NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLY91C** is Designed for 28 V Large Signal Class A,B and C Amplifier Applications up to 175 MHz.

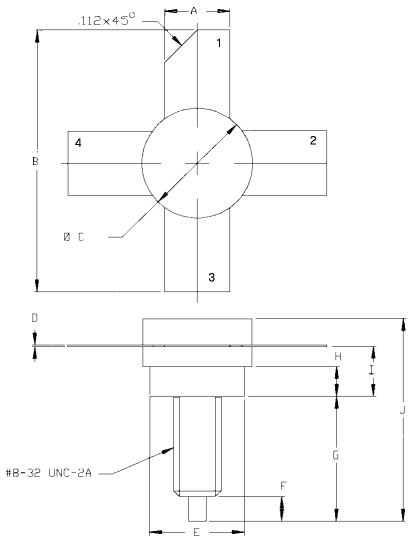
FEATURES INCLUDE:

- Emitter Ballasting
- Gold Metalization
- **3/8" SOE** Stud Package

MAXIMUM RATINGS

I_C	1.0 A
V_{CE}	35 V
V_{CB}	65 V
P_{DISS}	20 W @ T_C = 25 °C
T_J	-65 °C to + 200 °C
T_{STG}	-65 °C to + 150 °C
θ_{JC}	8.7 °C/W

PACKAGE STYLE .380" 4L STUD



	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	220/5,59	.230/5,84
B	980/24,89	
C	370/9,40	.385/9,78
D	004/0,10	.007/0,18
E	320/8,13	.330/8,38
F	100/2,54	.130/3,30
G	450/11,43	490/12,45
H	.090/2,29	.100/2,54
I	.155/3,94	.175/4,45
J		.750/19,05

1 = COLLECTOR 2 & 4 = EMITTER
3 = BASE

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I_C = 200 mA	65			V
BV_{CEO}	I_C = 10 mA	35			V
BV_{EBO}	I_E = 1.0 mA	4.0			V
I_{CES}	V_{CE} = 36 V			1.0	mA
h_{FE}	V_{CE} = 5.0 V I_C = 400 mA	10		100	---
C_{OB}	V_{CB} = 30 V f = 1.0 MHz			15	pF
P_G	V_{CC} =28 V P_{OUT} = 8.0 W f = 175 MHz	12.0	13.0		dB
η_C		65			%